



60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C	
60V	$2.7m\Omega$ @ V _{GS} = 10V	170A	

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Switching
- · Synchronous rectifications
- DC-DC converters

PowerDI5060-8/SWP (Type UX)



Top View Bottom View

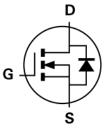
Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH62M7SPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

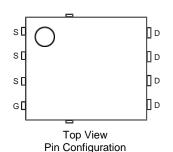
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.097 grams (Approximate)







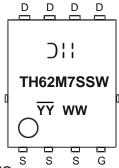
Ordering Information (Note 4)

Part Number	Packago	Packing		
Fait Number	Раскаде	Qty.	Carrier	
DMTH62M7SPSWQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



☐ H = Manufacturer's Marking
TH62M7SSW = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 23 = 2023)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Ocationary Paris Comment V 40V (Note 0)	Tc = +25°C		170	А
Continuous Drain Current, V _{GS} = 10V (Note 6)	T _C = +100°C	lD	120	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ірм	680	А	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	170	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	lsм	680	Α	
Avalanche Current, L = 0.2mH	I _{AS}	45	Α	
Avalanche Energy, L = 0.2mH	Eas	202	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	50	°C/W
Total Power Dissipation (Note 6)	$T_{C} = +25^{\circ}C$	P_{D}	150	W
Thermal Resistance, Junction to Case (Note 6)	Rejc	1	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

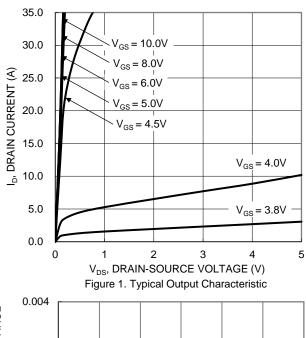
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_{D} = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	2.1	2.7	mΩ	Vgs = 10V, ID = 30A	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		4973			V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	1	1613	_	pF		
Reverse Transfer Capacitance	Crss	-	86	_			
Gate Resistance	Rg	_	0.81	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	68.7	_		V _{DD} = 30V, I _D = 30A,	
Gate-Source Charge	Qgs	_	16.3	_	nC		
Gate-Drain Charge	Q _{qd}		14.1	_		V _{GS} = 10V	
Turn-On Delay Time	t _D (ON)	_	11.45	_			
Turn-On Rise Time	t _R		10.68	_		$V_{DD} = 30V$, $V_{GS} = 10V$, $I_{D} = 30A$, $R_{g} = 3.5\Omega$	
Turn-Off Delay Time	tD(OFF)		33.01	_	ns		
Turn-Off Fall Time	tF	_	14.86	_	1	_	
Reverse Recovery Time	t _{RR}	_	53.34	_	ns		
Reverse Recovery Charge	QRR		90.49	_	nC	I _F = 30A, di/dt = 100A/μs	

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







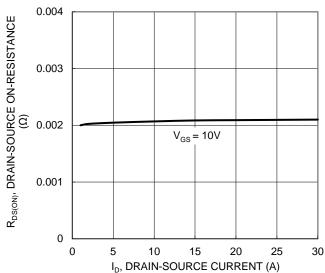


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

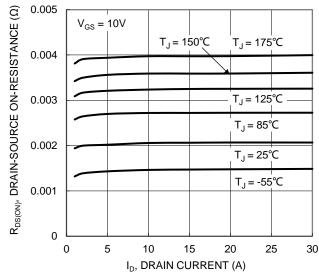


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

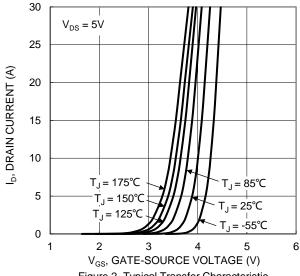


Figure 2. Typical Transfer Characteristic

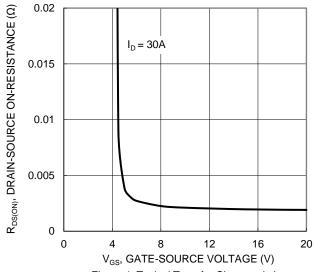


Figure 4. Typical Transfer Characteristic

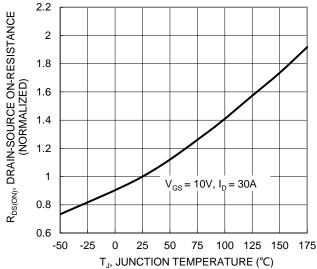
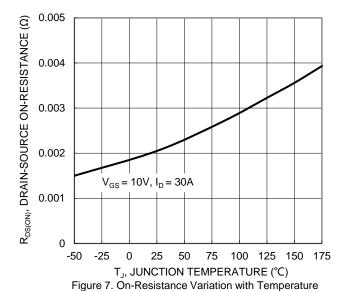
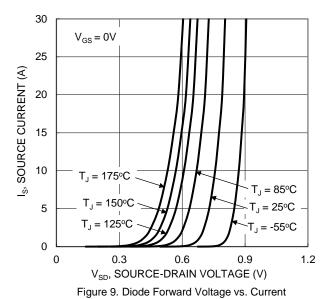
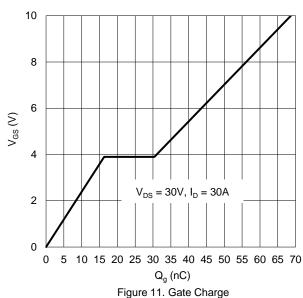


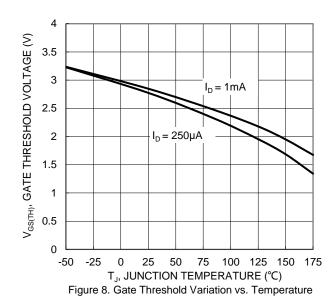
Figure 6. On-Resistance Variation with Junction Temperature

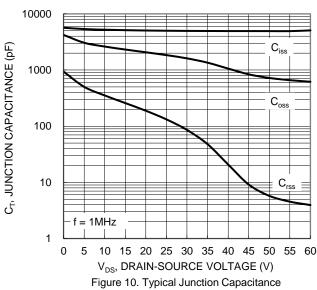


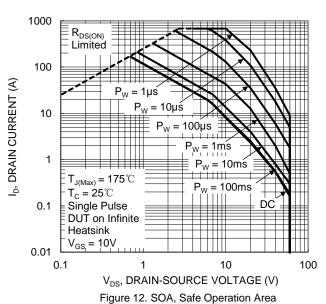














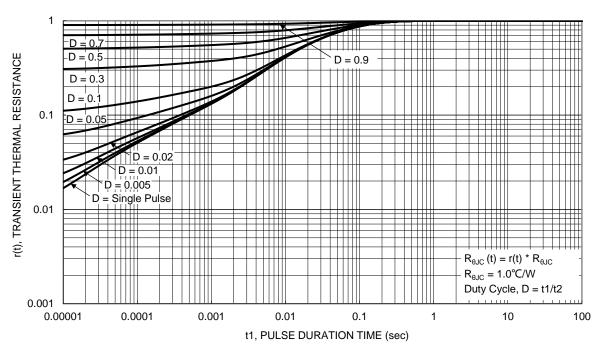


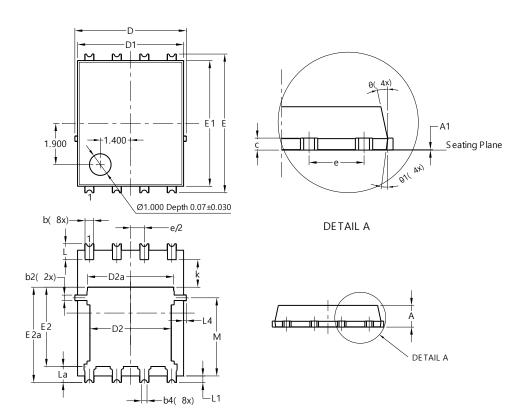
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)

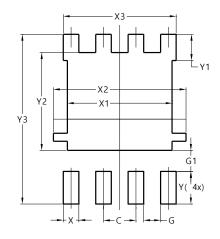


PowerDI5060-8/SWP (Type UX)					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4).25REF	-		
С	0.230	0.330	0.277		
D	5	.15 BS0)		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
E	6	.40 BS0	2		
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1.27BSC				
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	5.190		
Х3	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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